

Final Product/Process Change Notification

Document #:FPCN21412X Issue Date: 9 August 2016

Title of Change:	Qualify ON Semiconductor Vietnam (OSV) as an additional site for Assembly/Test of Trench Schottky TO220DG packaged products.		
Proposed first ship date:	9 November 2016		
Contact information:	Contact your local ON Semiconductor Sales Office or <phuong.hoang@onsemi.com></phuong.hoang@onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or < Phuong.Hoang @onsemi.com>		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>		
Change Part Identification:	Products from ON Semiconductor Vietnam (OSV) will be marked with site code "VN" prior to the date code.		
Change category:	☐ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other		
Change Sub-Category(s): ☐ Manufacturing Site Change/ ☐ Manufacturing Process Chan			
Sites Affected: All site(s) not ap	pplicable ON Semiconductor site(s): External Foundry/Subcon site(s) ON Dong Nai Province, Vietnam SP Semiconductor & Communication		

Description and Purpose:

This is the Final Notification to announce plans to qualify ON Semiconductor Vietnam (OSV) as an additional Assembly and Test site for operations of discrete TO220DG packaged products.

The Trench Schottky products are currently built at Nantong Fujitsu and Nantong Huada. Upon the expiration of this FPCN, Trench Schottky products in TO220DG package can be processed at the ON Semiconductor Vietnam location. The TO220DG products built in OSV will utilize a different mold compound described in the following table:

Piece part	Nantong Fujitsu	Nantong Huada	OSV
Mold compound	SI7200DX2 / E500HA	KL-G100	CV4180SV

ON Semiconductor Vietnam (OSV) is a qualified site for TO220DG Standard discrete packaged products and is ISO TS16949 certified.

Products sourced from OSV have been qualified to Consumer requirements and will continue to be Pb-free, Halide free and RoHS compliant.

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Reliability Data Summary:

QV DEVICE NAME: NTST40H120CTG

PACKAGE: TO220DG

Test	Specification	Condition	Interval	Result
HTRB	JESD22-A108	Ta = 90 °C, bias = 80% of rated V	1008 hrs	0/240
HTSL	JESD22-A103	Ta = 150 °C	1008 hrs	0/240
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 3.5min	8572 cyc	0/240
TC	JESD22-A104	Temp = -65°C to +150°C	1000 cyc	0/240
AC	JESD22-A102	121°C, 100% RH, 15psig, unbiased	96 hrs	0/240
H3TRB	JESD22-A101	Temp = 85°C, RH = 85%, bias = 100V max	1008 hrs	0/240
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/90
SD	JSTD002	Ta = 245°C, 10 sec		0/45

Electrical Characteristic Summary:

Electrical characteristics are not impacted.

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ist of affected Standard Parts:	
Part Number	Qualification Vehicle
NRTST40H100CTG	NTST40H120CTG
NRTSV20H100CTG	NTST40H120CTG
NRTSV30H120CTG	NTST40H120CTG
NTST20100CTG	NTST40H120CTG
NTST20120CTG	NTST40H120CTG
NTST20U100CTG	NTST40H120CTG
NTST30100CTG	NTST40H120CTG
NTST30120CTG	NTST40H120CTG
NTST30U100CTG	NTST40H120CTG
NTST30U100CTH	NTST40H120CTG
NTST40100CTG	NTST40H120CTG
NTST40120CTG	NTST40H120CTG
NTST40120CTH	NTST40H120CTG
NTST40H120CTG	NTST40H120CTG
NTST40H120ECTG	NTST40H120CTG
NTST60100CTG	NTST40H120CTG
NTSV20100CTG	NTST40H120CTG
NTSV20120CTG	NTST40H120CTG
NTSV20H120CTG	NTST40H120CTG
NTSV20H120ECTG	NTST40H120CTG
NTSV20U100CTG	NTST40H120CTG
NTSV20U80CTG	NTST40H120CTG
NTSV30100CTG	NTST40H120CTG
NTSV30100CTH	NTST40H120CTG
NTSV30100SG	NTST40H120CTG
NTSV30120CTG	NTST40H120CTG
NTSV30H100CTG	NTST40H120CTG
NTSV30H100ECTG	NTST40H120CTG

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